Analog Power

AM5521C

N & P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DFN2X3 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY $V_{DS}(V)$ $\mathbf{r}_{\mathrm{DS(on)}}\left(\Omega\right)$ $\mathbf{I}_{\mathbf{D}}(\mathbf{A})$ $0.058 @ V_{GS} = 4.5V$ 5 20 $0.077 @ V_{GS} = 2.5V$ 4.3 $0.064 @ V_{GS} = -4.5V$ -4.7 -20 $0.085 @ V_{GS} = -2.5V$ -4.1 DFN2x3 Top View S1 1 8 🖽 D, 7 🗖 D, G1 🗖 2 S2 🗔 3 6 🖽 D₂ Ď, S 5 🖽 D₂ G2 4 N-Channel MOSFET P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C UNLESS OTHERWISE NOTED)							
Parameter		Symbol	N-Channel	P-Channel	Units		
Drain-Source Voltage		V _{DS}	20	-20	v		
Gate-Source Voltage		V _{GS}	±8	±8	v		
	$T_A=25^{\circ}C$	I _D	5	-4.7			
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$		4.1	-3.9	А		
Pulsed Drain Current ^b		I _{DM}	8	-8			
Continuous Source Current (Diode Conduction) ^a			4.5	-4.5	Α		
	$T_A=25^{\circ}C$	П	2.1		w		
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	PD	1				
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 te	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	р	62.5	°C/W		
	Steady State	$R_{\theta JA}$	80	°C/W		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Limits Ch Min Typ Max				Unit	
Static	<i>J</i>			Min	Тур	Max		
State		VGS = VDS, $ID = 250 uA$	N	1		1	<u> </u>	
Gate-Threshold Voltage	V _{GS(th)}	$V_{GS} = V_{DS}, ID = -250 \text{ uA}$ $V_{GS} = V_{DS}, ID = -250 \text{ uA}$	P	-1			v	
	Ţ	$V_{DS} = 0 V, V_{GS} = 8 V$	N	-		100		
Gate-Body Leakage Current	I _{GSS}	$V_{DS} = 0 V, V_{GS} = -8 V$	Р			-100	μA	
		$V_{DS} = 16 V, V_{GS} = 0 V$	Ν			1	۸	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 V$, $V_{GS} = 0 V$	Р			-1	μA	
Zero Gate Voltage Drain Current	DSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$	Ν			10	μA	
		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$	Р			-10	μΛ	
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	Ν	5			А	
	¹ D(on)	$V_{DS} = -5 V, V_{GS} = -4.5 V$	Р	-5			A	
		$V_{GS} = 4.5 V, I_D = 1 A$	Ν			0.058		
Drain-Source On-Resistance ^A	r	$V_{GS} = -4.5 V, I_{D} = 1 A$	Р			0.077	Ω	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 2.5 V, I_{D} = 1 A$	Ν			0.064		
		$V_{GS} = -2.5 V, I_{D} = -1 A$	Р			0.085		
		$V_{DS} = 5 V, I_D = 1 A$	Ν		10		S	
Forward Tranconductance ^A	$g_{\rm fs}$	$V_{DS} = -5 V, I_{D} = 1 A$	Р		5			
	V	$I_{S} = 1 A, V_{GS} = 0 V$	Ν		0.80		S	
Diode Forward Voltage ^A	V_{SD}	$I_{s} = -1 A, V_{GS} = 0 V$	Р		-0.83		2	
Dynamic ^b								
Total Gate Charge Q			N P		2 7			
	-	N-Channel V_{DS} =15V, V_{GS} =4.5V, I_{D} =1A	P N		0.4		nC	
Gate-Source Charge	Q_{gs}	$V_{DS}=15V$, $V_{GS}=4.5V$, $1_D=1A$ P-Channel	P		1			
Gate-Drain Charge	Q _{gd}	VDS=-15V, VGS=-4.5V, ID=-1A	Ν		0.7			
Gate-Drain Charge	√gd		Р		2			
Turn-On Delay Time	t _{d(on)}	N-Chaneel	N P		6 10			
		V_{DD} =15V, V_{GS} =4.5V, I_D =1A ,	N		9		nS	
Rise Time	t _r	$R_{GEN}=15\Omega$,	Р		1			
Turn-Off Delay Time	t _{d(off)}	P-Channel	N		5			
	u(011)	V_{DD} =-15V, V_{GS} =-4.5V, I_{D} =-1A R _{GEN} =15 Ω	P N		11 16			
Fall-Time	t _f	KGEN=1322	P N		10			

Notes

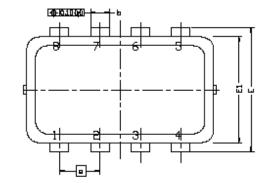
a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.

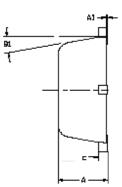
b. Guaranteed by design, not subject to production testing.

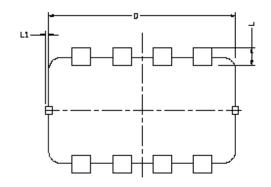
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Package Information







חות.	MILLIMETERS			INCHES			
	MIN	Ĩ	MAX	MIN	NOM	MAX	
A	Q700	0.80	DOBIO	0.0276	0.0315	0.0334	
Al	0.00		002	Q.0Q0		0. 0 02	
b	0.24	0.30	135	0.019	0.012	0.014	
С	0,08	0.152	125	0013	0.006	0.010	
D	3.00 BSC			0.118 BSC			
Ε	2.00 BSC			0079 BSC			
E1	1.70 BSC			0.067 BSC			
6	¢	.65 BS	C	0.026 BSC			
L	0.20	0.275	0.400	0000	0.011	0.0157	
L1	Ō	-	0.100	Ö		0.004	
81	Ŭ°	Ць	12*	Ċ"	10*	12*	